

SOI MOSFET WITH MULTI-SIDED SOURCE/DRAIN SILICIDE**ABSTRACT**

A microelectronic device including an insulator located over a substrate, a semiconductor feature and a contact layer. The semiconductor feature has a thickness over the insulator, a first surface opposite the insulator, and a sidewall spanning at least a portion of the thickness. The contact layer has a first member extending over at least a portion of the first surface and a second member spanning at least a portion of the sidewall.